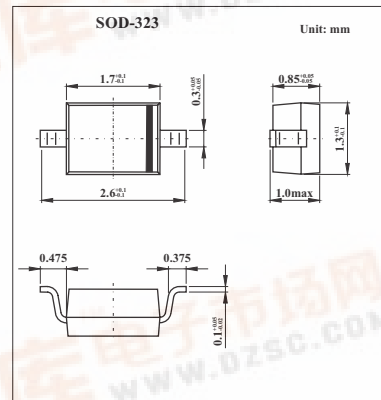


SMD Type Diodes

## Silicon Schottky Diode BAT14-03W

■ Features

- DBS mixer application to 12GHz
- Medium barrier type
- Low capacitance



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V <sub>R</sub>	4	V	
Forward current	I <sub>F</sub>	90	mA	
Operating temperature range	T <sub>op</sub>	-55 to +125	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150		
Total power dissipation	T <sub>s</sub> ≤ 85 °C	P <sub>tot</sub>	100	mW
Junction ambient <sup>(1)</sup>	R <sub>thJA</sub>	≤ 450	°C	
Junction-soldering point	R <sub>thJS</sub>	≤ 690	K/W	

Note:

1. Package mounted on an epoxy pcb 40 mm × 40 mm × 15 mm/1cm<sup>2</sup> Cu.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Min	Typ	Max	Unit	
Breakdown Voltage	I <sub>(BR)</sub> = 5 μA	V <sub>(BR)</sub>	4		V	
Forward voltage	I <sub>F</sub> = 1 mA	V <sub>F</sub>	0.36	0.43	0.52	V
	I <sub>F</sub> = 10 mA		0.48	0.55	0.66	
Diode capacitance	V <sub>R</sub> = 0; f = 1 MHz	C <sub>T</sub>		0.22	0.35	pF
Differential forward resistance	I <sub>F</sub> = 10 mA/50 mA	R <sub>F</sub>		5.5		Ω

■ Marking

Marking	○
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